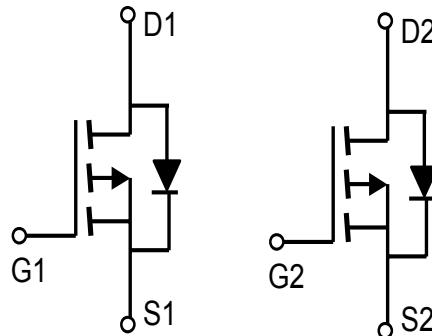


General Description

The AO4805 uses advanced trench technology to provide excellent $R_{DS(ON)}$, and ultra-low low gate charge with a 25V gate rating. This device is suitable for use as a load switch or in PWM applications.



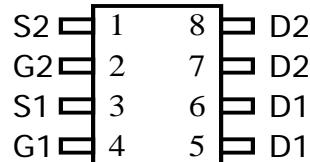
Features

V_{DS} (V) = -30V

I_D = -9A

$R_{DS(ON)} < 15m\Omega$ ($V_{GS} = 10V$)

$R_{DS(ON)} < 19m\Omega$ ($V_{GS} = 4.5V$)



Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current ^A	$T_A=25^\circ C$	I_D	-8	A
Current ^A	$T_A=70^\circ C$		-6.9	
Pulsed Drain Current ^B		I_{DM}	-40	
Power Dissipation ^A	$T_A=25^\circ C$	P_D	2	W
	$T_A=70^\circ C$		1.44	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$t \leq 10s$	$R_{\theta JA}$	50	62.5	°C/W
Maximum Junction-to-Ambient ^A	Steady-State		73	110	°C/W
Maximum Junction-to-Lead ^C	Steady-State	$R_{\theta JL}$	31	40	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=-250\mu\text{A}, V_{GS}=0\text{V}$	-30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-24\text{V}, V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			-1	μA
					-5	
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}, V_{GS}=\pm20\text{V}$			±100	nA
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu\text{A}$	-1	-1.5	-2.5	V
$I_{\text{D(ON)}}$	On state drain current	$V_{GS}=-10\text{V}, V_{DS}=-5\text{V}$	40			A
$R_{\text{DS(ON)}}$	Static Drain-Source On-Resistance	$V_{GS}=-10\text{V}, I_D=-8\text{A}$		12	15	$\text{m}\Omega$
		$V_{GS}=-4.5\text{V}, I_D=-5\text{A}$		16	19	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS}=-5\text{V}, I_D=-8\text{A}$	16	21		S
V_{SD}	Diode Forward Voltage	$I_S=-1\text{A}, V_{GS}=0\text{V}$		-0.75	-1	V
I_S	Maximum Body-Diode Continuous Current				-2.6	A
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}, V_{DS}=-15\text{V}, f=1\text{MHz}$		2076		pF
C_{oss}	Output Capacitance			503		pF
C_{rss}	Reverse Transfer Capacitance			302		pF
R_g	Gate resistance	$V_{GS}=0\text{V}, V_{DS}=0\text{V}, f=1\text{MHz}$		2		Ω
Q_g	Total Gate Charge	$V_{GS}=-10\text{V}, V_{DS}=-15\text{V}, I_D=-8\text{A}$		39		nC
Q_{gs}	Gate Source Charge			8		nC
Q_{gd}	Gate Drain Charge			11.4		nC
$t_{\text{D(on)}}$	Turn-On DelayTime	$V_{GS}=-10\text{V}, V_{DS}=-15\text{V}, R_L=1.8\Omega, R_{\text{GEN}}=3\Omega$		12.7		ns
t_r	Turn-On Rise Time			7		ns
$t_{\text{D(off)}}$	Turn-Off DelayTime			25.2		ns
t_f	Turn-Off Fall Time			12		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=-8\text{A}, dI/dt=100\text{A}/\mu\text{s}$		32		ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=-8\text{A}, dI/dt=100\text{A}/\mu\text{s}$		26		nC

A: The value of R_{0JA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any given application depends on the user's specific board design. The current rating is based on the $t \leq 10\text{s}$ thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R_{0JA} is the sum of the thermal impedance from junction to lead R_{0JL} and lead to ambient.

D: The static characteristics in Figures 1 to 6,12,14 are obtained using 80 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

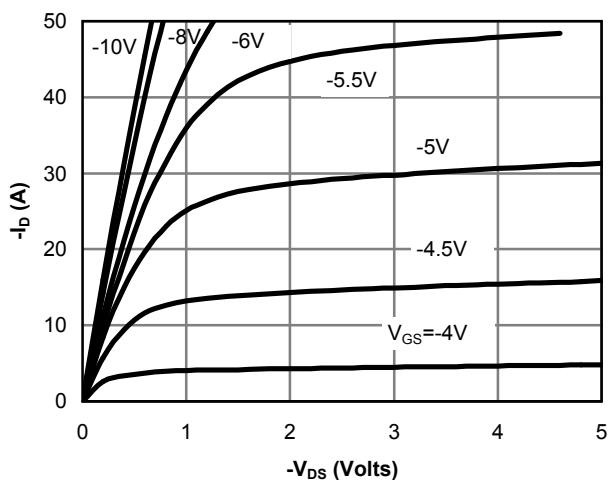


Fig 1: On-Region Characteristics

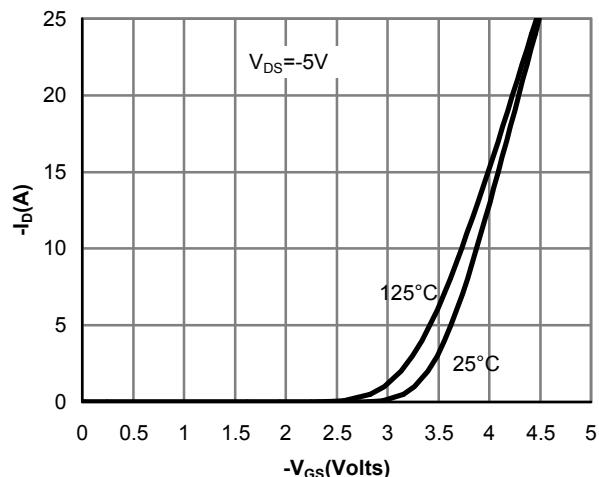


Figure 2: Transfer Characteristics

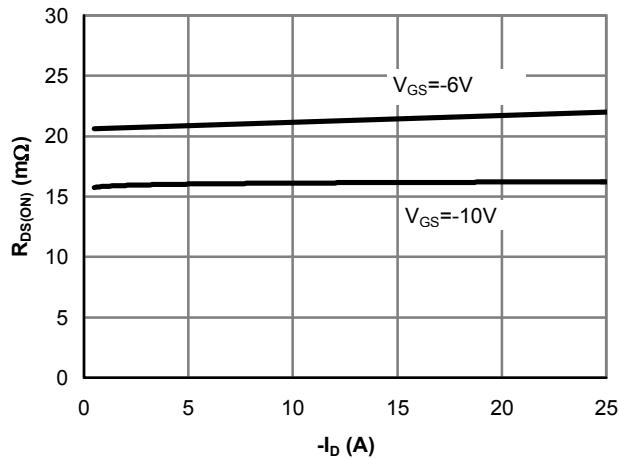


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

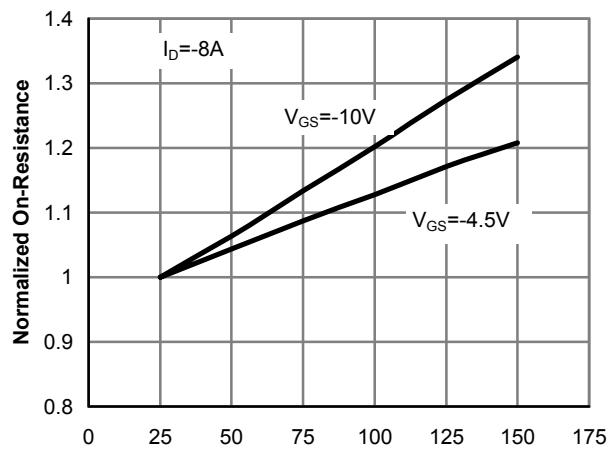


Figure 4: On-Resistance vs. Junction Temperature

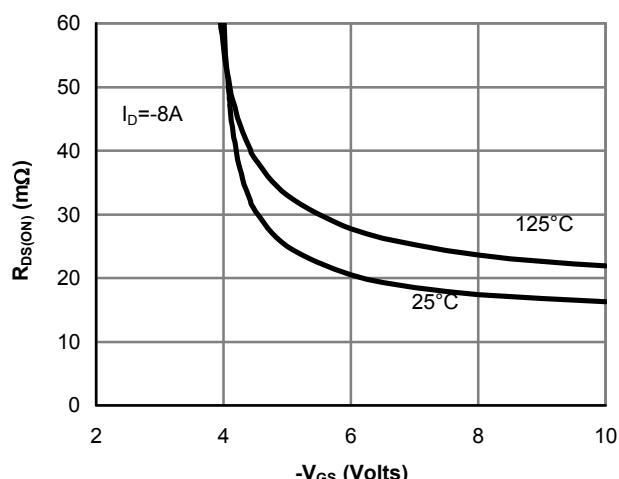


Figure 5: On-Resistance vs. Gate-Source Voltage

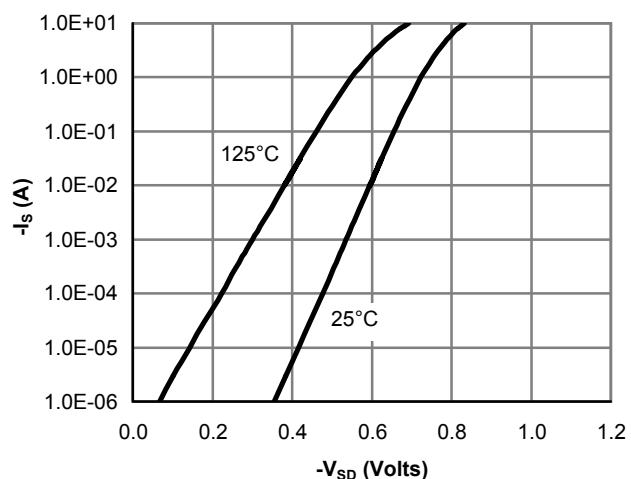
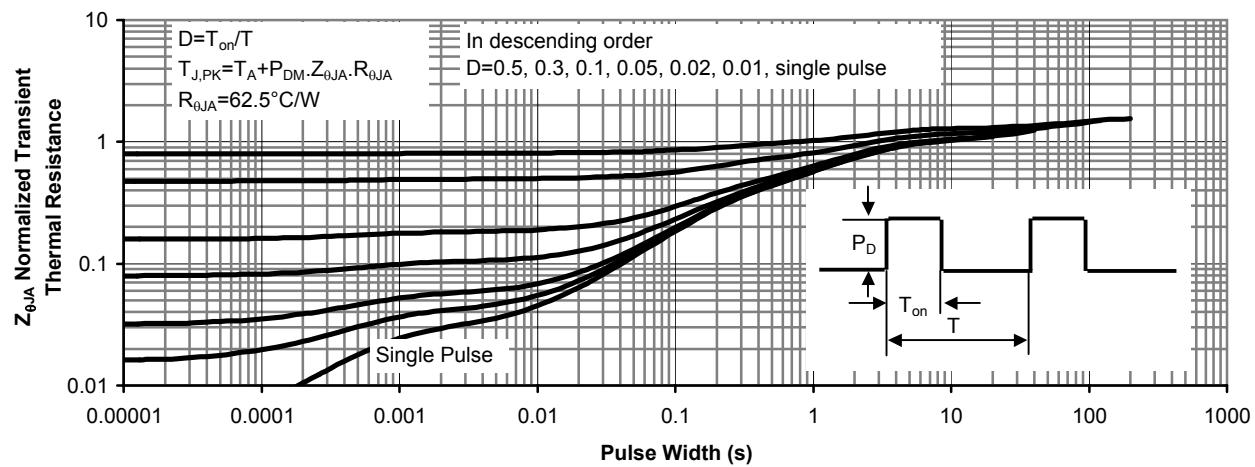
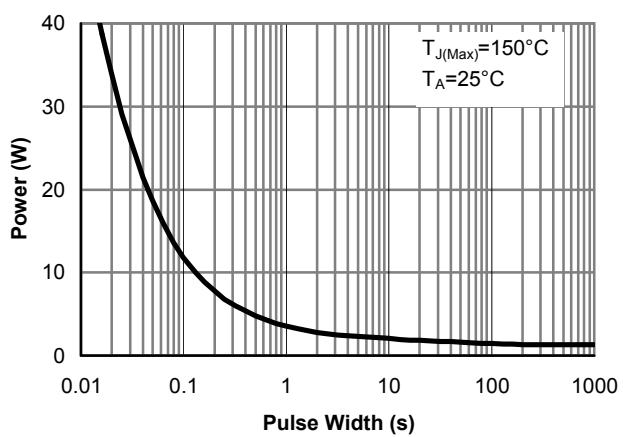
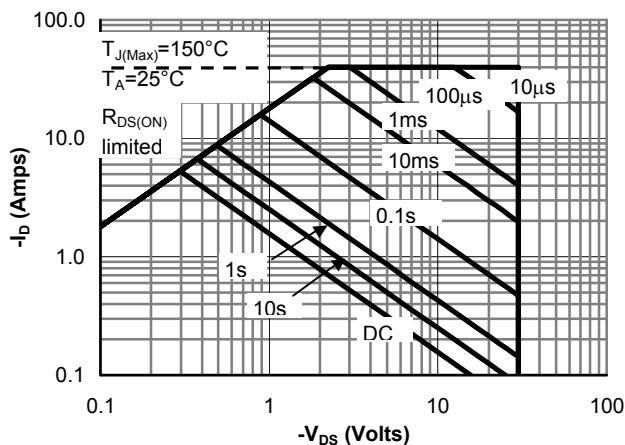
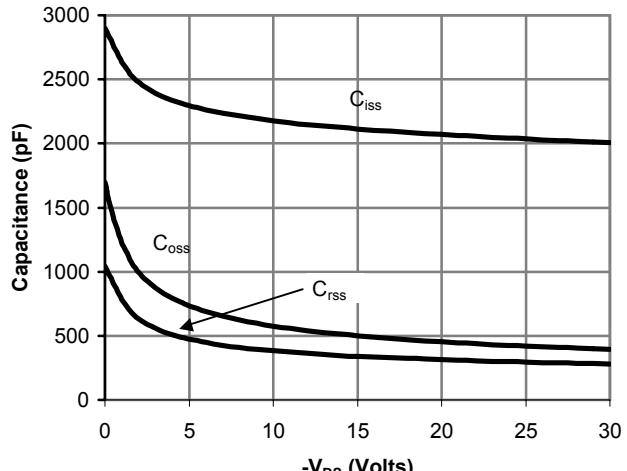
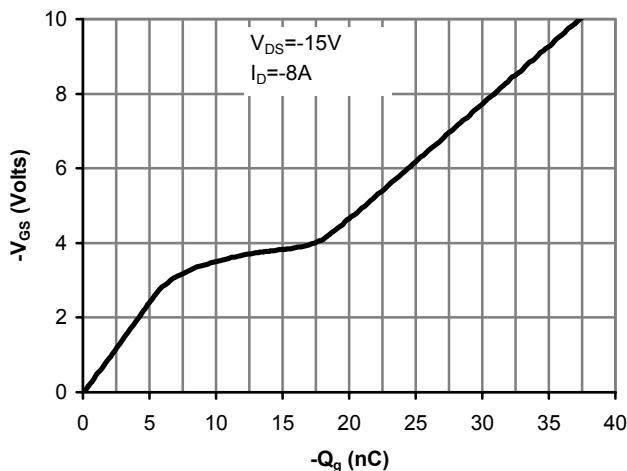


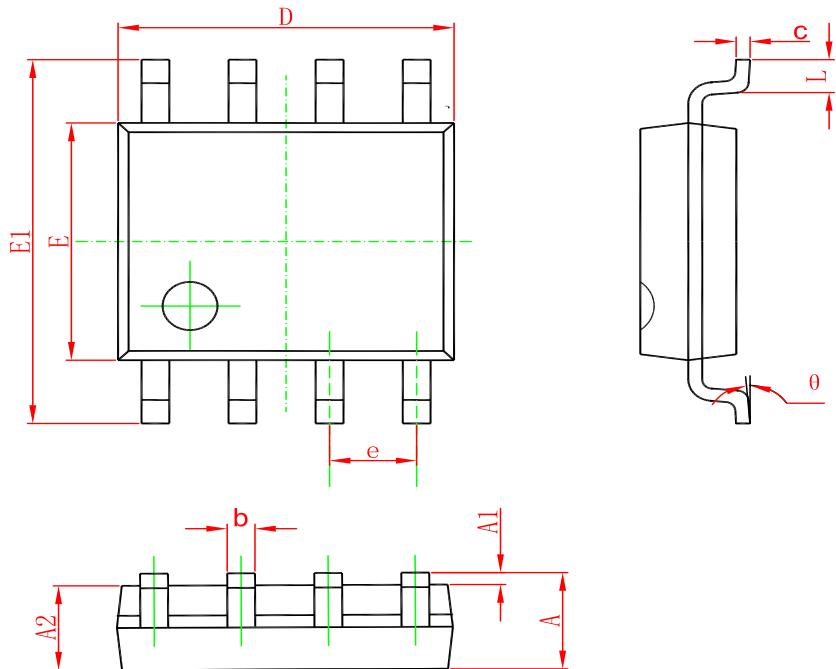
Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



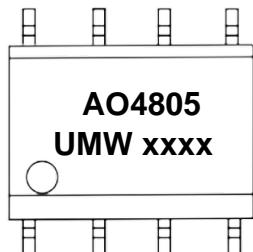
PACKAGE OUTLINE DIMENSIONS

SOP-8



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

Marking



("xxxx"代表年份周期)

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